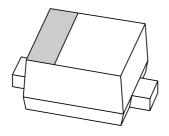
## DISCRETE SEMICONDUCTORS

## DATA SHEET



# **1PS79SB63**Schottky barrier diode

**Product specification** 

2002 Apr 08





## Schottky barrier diode

1PS79SB63

#### **FEATURES**

- · Very low capacitance
- · Low forward voltage
- Ultra small plastic SMD package.

## **APPLICATIONS**

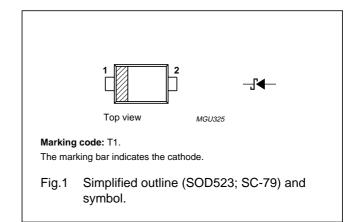
- High frequency detection
- Ultra high-speed switching
- · Zero bias detection.

## **DESCRIPTION**

Planar Schottky barrier diode encapsulated in a SOD523 (SC-79) ultra small plastic SMD package. ESD sensitive device, observe handling precautions.

#### **PINNING**

PIN	DESCRIPTION	
1	cathode	
2	anode	



## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	5	V
I <sub>F</sub>	continuous forward current		_	20	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta = 0.25$	_	400	mA
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8.3 ms half sine wave; JEDEC method	_	550	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

## **CAUTION**

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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## **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.2			
		I <sub>F</sub> = 0.1 mA	160	200	mV
		I <sub>F</sub> = 1 mA	240	300	mV
I <sub>R</sub>	continuous reverse current	see Fig.3			
		V <sub>R</sub> = 1 V	0.4	1	μΑ
		V <sub>R</sub> = 5 V; note 1	_	50	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0 V; f = 1 MHz; see Fig.4	0.35	0.5	pF
L <sub>s</sub>	series inductance		0.6	_	nH

## Note

1. Pulse test: pulse width = 300  $\mu$ s;  $\delta$  = 0.02.

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	450	K/W

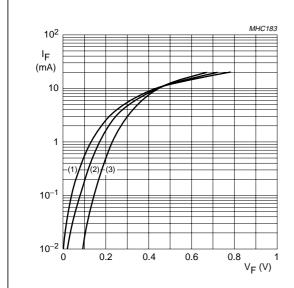
## Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

## Schottky barrier diode

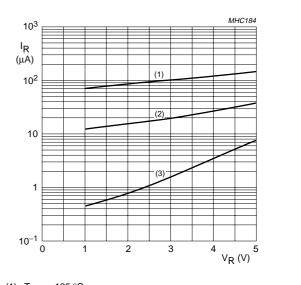
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## **GRAPHICAL DATA**



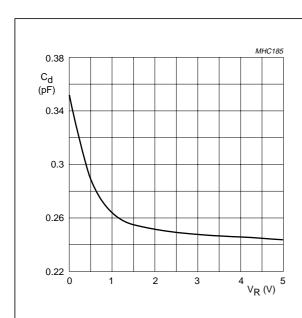
- (1)  $T_{amb} = 125 \,^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



- (1)  $T_{amb} = 125 \,^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}.$ 

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

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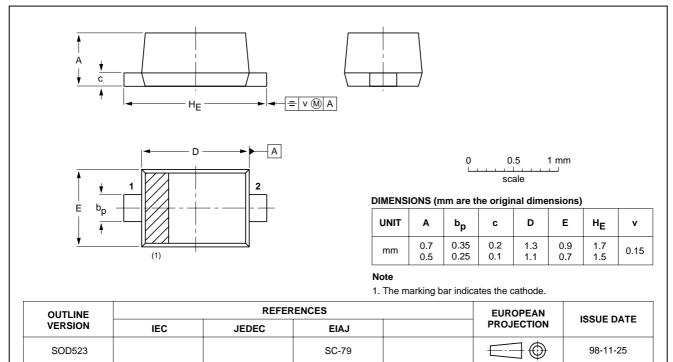
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## **PACKAGE OUTLINE**

## Plastic surface mounted package; 2 leads

**SOD523** 



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#### **DATA SHEET STATUS**

DATA SHEET STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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NOTES

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